

AMENDMENTS TO THE CLAIMS:

If entered, this listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1 - 16. (Canceled)

17. (Previously Presented) A MOSFET device comprising:

a gate comprising a polysilicon trace overlying a semiconductor substrate with an insulator therebetween;

a source region and a drain region in said

5 semiconductor substrate with said polysilicon trace laterally between said source and drain regions;

a liner oxide layer overlying said polysilicon trace wherein said liner oxide layer covers sidewalls of

said polysilicon trace at said source and drain regions and

10 wherein said liner oxide layer covers the top of said polysilicon trace; and

silicon nitride spacers wherein said liner oxide layer is laterally between said silicon nitride spacers and

said polysilicon trace at said source and drain regions and

15 wherein said silicon nitride spacer has an L-shaped

CS-99-063B
profile.

18. (Original) The device according to Claim 17 wherein said liner oxide layer has a thickness of between about 50 Angstroms and 300 Angstroms.

19. (Canceled)

20. (Canceled)

21. (Previously Presented) The device according to Claim 17 wherein said silicon nitride layer is formed by one of the group of: growing by thermal process and depositing by chemical vapor deposition.

22. (Previously Presented) A MOSFET device comprising:

a gate comprising a polysilicon trace overlying a semiconductor substrate with an insulator therebetween;

a source region and a drain region in said semiconductor substrate with said polysilicon trace laterally between said source and drain regions;

a liner oxide layer overlying said polysilicon trace wherein said liner oxide layer covers sidewalls of said polysilicon trace at said source and drain regions and

10 wherein said liner oxide layer covers the top of said polysilicon trace; and

silicon nitride spacers wherein said liner oxide layer is laterally between said silicon nitride spacers and said polysilicon trace at said source and drain regions, wherein
15 said silicon nitride spacers have an L-shaped profile, and wherein said silicon nitride layer is formed by one of the group of: growing by thermal process and depositing by chemical vapor deposition.

23. (Previously Presented) The device according to Claim
22 wherein said liner oxide layer has a thickness of between about 50 Angstroms and 300 Angstroms.

24. (Canceled)

25. (Canceled)

26. (Previously Presented) A MOSFET device comprising:

a gate comprising a polysilicon trace overlying a semiconductor substrate with an insulator therebetween;
a source region and a drain region in said
5 semiconductor substrate with said polysilicon trace laterally between said source and drain regions;

a liner oxide layer overlying said polysilicon trace
wherein said liner oxide layer covers sidewalls of said
polysilicon trace at said source and drain regions and
10 wherein said liner oxide layer covers the top of said
polysilicon trace; and

silicon nitride spacers wherein said liner oxide layer
is laterally between said silicon nitride spacers and said
polysilicon trace at said source and drain regions, wherein
15 said silicon nitride spacers have an L-shaped profile, and
wherein said silicon nitride layer is formed by chemical
vapor deposition.

27. (Previously Presented) The device according to Claim 26
wherein said liner oxide layer has a thickness of between
about 50 Angstroms and 300 Angstroms.

28. (Canceled)